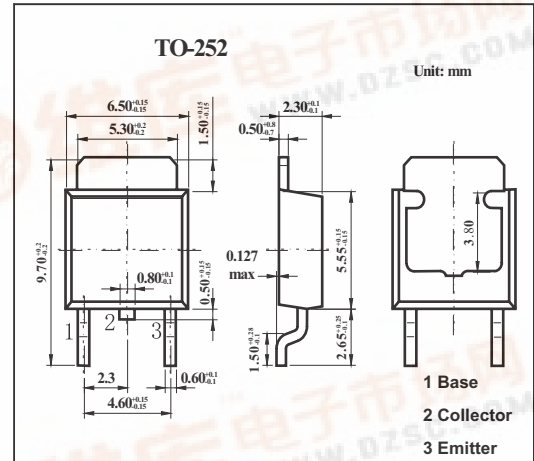


SMD Type Transistors

NPN Silicon Epitaxial Transistor
2SC3075

■ Features

- Excellent Switching Times
tr=1.0μs (Max.) tr=1.5μs (Max.) at Ic=0.5A
- High collector Breakdown Voltage: VCE0=400V



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	500	V
Collector to emitter voltage	V _{CE0}	400	V
Emitter to base voltage	V _{EBO}	7	V
Collector current (DC)	I _c	0.8	A
Collector current (Pulse)	I _{cp}	1.5	A
Base Current	I _B	0.5	A
Total Power dissipation Ta = 25°C	P _c	1	W
T _c = 25°C		10	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cutoff current	I _{CBO}	V _{CB} =400V, I _E =0			100	μA
emitter cutoff current	I _{EBO}	V _{EB} =7V, I _C =0			100	μA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	500			V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	400			V
DC current Gain	h _{FE}	V _{CE} =5V, I _C =0.1A	20		100	
		V _{CE} =5V, I _C =0.5A	10			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =0.1A, I _B =0.01A			0.5	V
Base- Emitter Voltage	V _{BE(sat)}	I _C =0.1A, I _B =0.01A			1	V
Switching time turn-On time	tr	<p>20 μs I_{B1} IN-PUT I_{B1} OUTPUT I_{B2} 400Ω V_{CC} = 200 V</p>			1	μs
Switching storage time	t _{stg}				2.5	μs
Switching fall time	tf		I _{B1} = -I _{B2} = 0.05 A, DUTY CYCLE ≤ 1%			1.5

